BFL4001

ON Semiconductor®

N-Channel Power MOSFET 900V, 6.5A, 2.7Ω, TO-220F-3FS

http://onsemi.com

Features

- ON-resistance RDS(on)= 2.1Ω (typ.)
- · 10V drive

• Input capacitance Ciss=850pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		900	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	6.5	Α
	I _{Dpack} *2	Tc=25°C (Our ideal heat dissipation condition)*3	4.1	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	13	Α
Allowable Power Dissipation	Do		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	37	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		223	mJ
Avalanche Current *5	IAV		6.5	Α

Note:*1 Shows chip capability

- *2 Package limited
- *3 Our condition is radiation from backside.

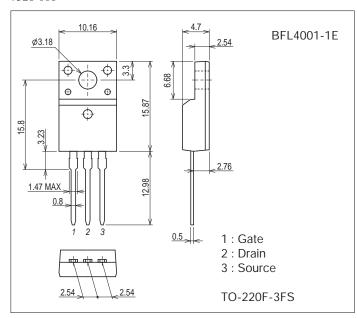
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=50V, L=10mH, IAV=6.5A
- *5 L≤10mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001



Product & Package Information

• Package : TO-220F-3FS

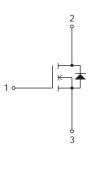
• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection





Semiconductor Components Industries, LLC, 2013

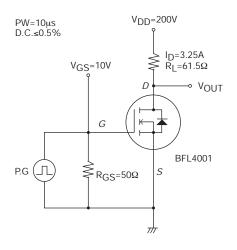
July, 2013

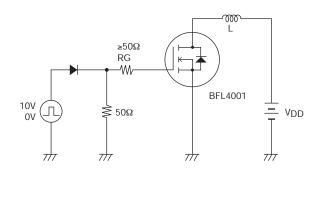
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	900			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =720V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.0		4.0	V
Forward Transfer Admittance	yfs	VDS=20V, ID=3.25A	1.8	3.6		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =3.25A, V _G S=10V		2.1	2.7	Ω
Input Capacitance	Ciss			850		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		130		pF
Reverse Transfer Capacitance	Crss			43		pF
Turn-ON Delay Time	t _d (on)			19		ns
Rise Time	t _r	See appointed Test Circuit		49		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		156		ns
Fall Time	tf			52		ns
Total Gate Charge	Qg			44		nC
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =6.5A		7.0		nC
Gate-to-Drain "Miller" Charge	Qgd			22		nC
Diode Forward Voltage	V _{SD}	I _S =6.5A, V _{GS} =0V		0.85	1.2	V

Switching Time Test Circuit

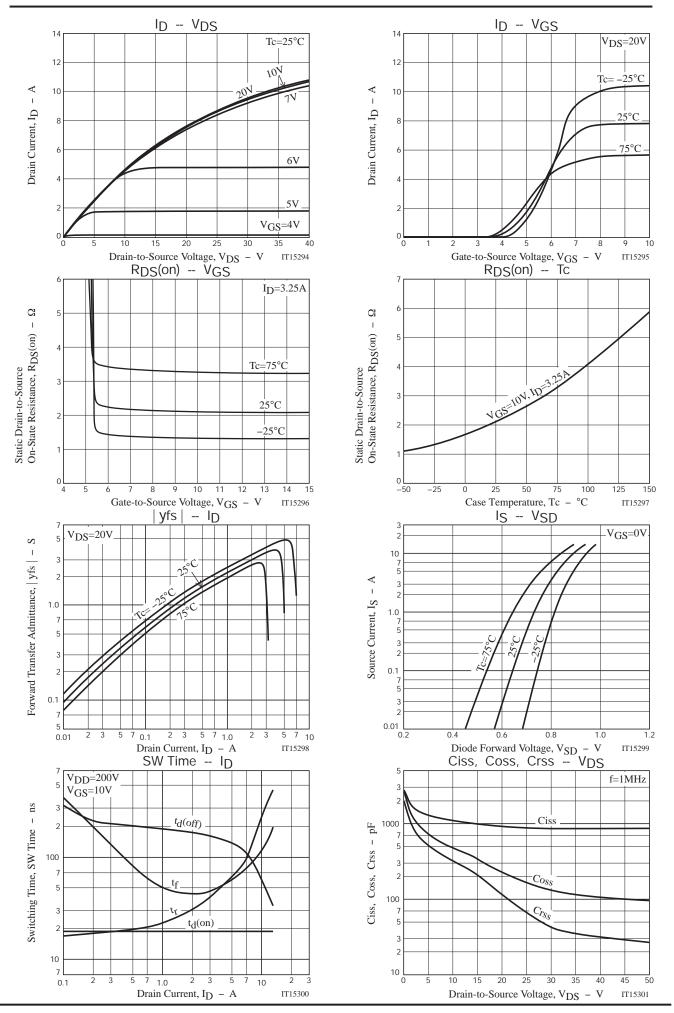
Avalanche Resistance Test Circuit

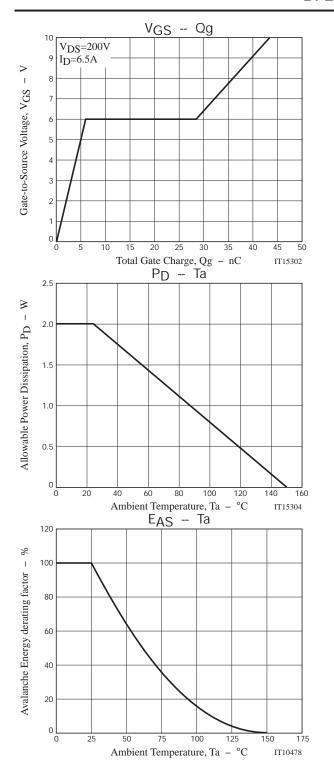


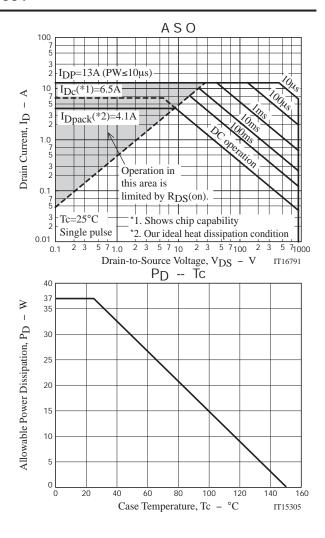


Ordering Information

Device	Package	Shipping	memo
BFL4001-1E	TO-220F-3FS	50pcs./magazine	Pb Free





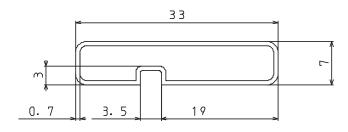


Magazine Specification

BFL4001-1E

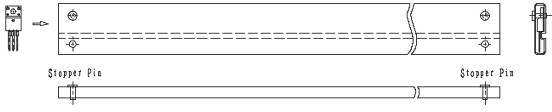
1. Packing Format

Package Name	Magazine Name	Maximum Number of devices contained (pcs)			Packing format		
1 4 4 4 5 4 1 4 4 4 4	Idagas ing Hams	I	Inner box	Outer box	Inner BOX	Outer BOX	
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dinensions:mm (external) 590×225×178	

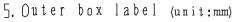


Tolerance=±(), 3mm
Thickness=(), 7±(), 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

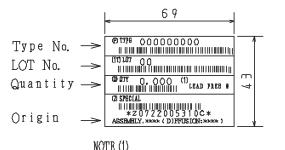
3. Storage method to magazine

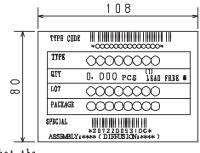


4. Inner box label (unit:mm)



It is a label at the time of factory shigments. The form of a label may change in physical distribution process.



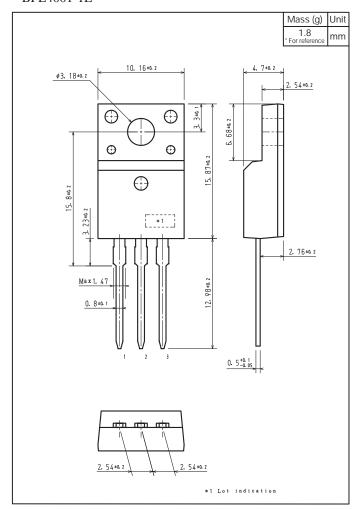


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

BFL4001-1E



Note on usage: Since the BFL4001 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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